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#7B  
Amatt.  
Sk Davis  
9/4/02

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :  
Ende SHAN, et al. : EXAMINER: TOLEDO, F.  
SERIAL NO.: 09/688,817 ✓ : GROUP ART UNIT: 2823  
FILED: OCTOBER 17, 2000 ✓ :  
FOR: LOW TEMPERATURE ✓ :  
METALLIZATION PROCESS :

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AUG 21 2002  
TECHNOLOGY CENTER 2800

AMENDMENT AND REQUEST FOR RECONSIDERATION

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

In response to the Official Action of February 14, 2002, reconsideration of the above-identified application is respectfully requested in view of the following amendment and remarks.

IN THE CLAIMS

✓  
Please amend the claims to read as follows:

- 
1. (Twice Amended) A method of forming a layer of metal on a substrate, comprising:
- B1
- i) depositing a seed layer of the metal on a first substrate surface which is Ti, said seed layer being sufficient to cover said first substrate surface which is Ti at a substrate temperature of from 220 to 300°C;